L Number	Hits	Search Text	DB	Time stamp
1	7756671	via or opening or trench or v-trench or groove or v-groove or contact or	USPAT;	2003/09/29 09:08
		recess or cavity or cavities or hole or damascene	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	289	(via or opening or trench or v-trench or groove or v-groove or contact or	USPAT;	2003/09/29 09:10
		recess or cavity or cavities or hole or damascene) and 216/37	US-PGPUB;	
			EPO; JPO;	
	7 411		DERWENT;	
			IBM TDB	
3	12	((via or opening or trench or v-trench or groove or v-groove or contact or recess or cavity or cavities or hole or damascene) and 216/37) and	USPĀT;	2003/09/29 10:05
			US-PGPUB;	
		438/734	EPO; JPO;	
			DERWENT,	
			IBM TDB	
5	O	438/638.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT;	2003/09/29 10:06
	v	, (, <u>B</u> 22 22 22 24 01040.2)	US-PGPUB;	-
			EPO; JPO;	
			DERWENT;	
		*	IBM TDB	
6	1646	438/637.ccls.	USPAT;	2003/09/29 10:06
			US-PGPUB;	2003/03/25 10:00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	0	438/637.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT;	2003/09/29 10:06
	Ŭ	150/057.0013. With (Oxygen of 02 of 03002 of 0.800,2)	US-PGPUB;	2003/09/29 10:00
			EPO; JPO;	
	i		DERWENT;	
			IBM_TDB	
4	543	438/638.ccls.	USPAT;	2003/09/29 11:27
	5-15	130/030.0013,	US-PGPUB;	2003/09/29 11.27
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	21	photoresist with low-k with (spin-on polymer)	USPAT;	2003/09/29 11:39
9	21	photoresist with low-k with (spin-on polymer)	US-PGPUB;	2003/09/29 11.39
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	15	photoresist with (spin-on adj polymer)	USPAT;	2003/09/29 11:42
	15	photoresist with (spin-on any polymer)	US-PGPUB;	2003/09/29 11.42
			EPO; JPO;	
			DERWENT;	
1				
10	742	photoresist with (low-k or (low adj dielectric) or silk or flare or (organic	IBM_TDB	2002/00/20 12:51
10	174	adj (ild dielectric interlayer)))	USPAT; US-PGPUB;	2003/09/29 12:51
		auj (iia diciccule iiiicitayet))	1	
			EPO; JPO;	
			DERWENT;	
11	79	(photoresist with (low-k or (low adj dielectric) or silk or flare or	IBM_TDB	2002/00/20 11:52
	13	(organic adj (ild dielectric interlayer)))) with (oxygen or o2 or	USPAT;	2003/09/29 11:53
		"o.sub.2")	US-PGPUB;	
	'	0.540,2)	EPO; JPO;	
			DERWENT;	
12	1341	(nattarns nearl photograph) with (assume as =2 == " ==1 2")	IBM_TDB	2002/00/20
12	1341	(pattern\$ near4 photoresist) with (oxygen or o2 or "o.sub.2")	USPAT;	2003/09/29 11:53
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

	1706	(/	TIODAT.	2002/00/20 11.55
13	1786	((remov\$4 near1 portion) or pattern\$4) with photoresist with (oxygen or	USPAT;	2003/09/29 11:55
		o2 or "o.sub.2")	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
14	70	(remov\$4 near1 portion) with photoresist with (oxygen or o2 or	USPAT;	2003/09/29 11:56
		"o.sub.2")	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	109	photoresist with (low-k or (low adj dielectric) or silk or flare) with	USPAT,	2003/09/29 12:51
	. 9	organic	US-PGPUB;	
			EPO; JPO;	å
			DERWENT;	
			IBM TDB	
16	19	(low-k or (low adj dielectric) or silk or flare) adj mask\$4	USPAT;	2003/09/29 12:52
		(· · · · · (· · · · · · · · · ·	US-PGPUB;	
			ЕРО; ЈРО;	
	4		DERWENT;	
			IBM TDB	
17	199	(low-k or (low adj dielectric)) near3 mask\$4	USPAT;	2003/09/29 12:52
	177	(10W-K of (10W day diefective)) fleat5 flidsk44	US-PGPUB;	2005/05/25 12.52
		*	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	48	((low-k or (low adj dielectric)) near3 mask\$4) with photoresist	USPAT;	2003/09/29 12:55
10	40	((10m-x or (10m and mercente)) hears mask \$4) with bilototesist	US-PGPUB;	2003103123 12.33
			1	
		*	EPO; JPO;	
		·	DERWENT;	
10	163	((law la a (law adi dialactria))	IBM_TDB	2002/00/00 10/55
19	151	((low-k or (low adj dielectric)) near3 mask\$4) not (((low-k or (low adj	USPAT;	2003/09/29 12:55
		dielectric)) near3 mask\$4) with photoresist)	US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	